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### U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
_____	AA					
_____	AB					
_____	AC					
_____	AD					
_____	AE					

### FOREIGN PATENT DOCUMENTS

Document No.	Date	Country	Translation (Yes or No)
<u>TN</u> AF 09246670A	9/19/97	Japan	Abstract only
<u>TN</u> AG 09307190A	11/28/97	Japan	Abstract only
<u>TN</u> AH 11168257A	6/22/99	Japan	Abstract only
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### OTHER DOCUMENTS

<u>TN</u>	AK	T. Asano et al.; "CW Operation of AlGaInN-GaN Laser Diodes"; <u>Physica Status Solidi (a)</u> ; Vol. 176, No. 1 (Nov. 1999); pp. 23-30.
<u>TN</u>	AI	S. Nunoue et al.; "Reactive Ion Beam Etching and Overgrowth Process in the Fabrication of InGaN Inner Stripe Laser Diodes"; <u>Japan Journal Applied Physics</u> ; Vol. 37 (March 1998); pp. 1470-73.
Examiner <u>Phan Nguyen</u> Date Considered <u>7-10-02</u>		